



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SD667, 2SD667A TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.9 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 1 A

Collector-base voltage

$V_{(BR)CBO}$: 120 V

Operating and storage junction temperature range

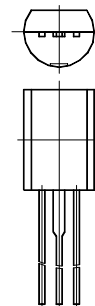
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92MOD

1. EMITTER

2. COLLECTOR

3. BASE



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ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	2SD6677	80		V
			2SD667A	100		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=100V, I_E=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=150mA$	2SD667	60	320	
			2SD667A	60	200	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=500mA$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			1	V
Base-emitter voltage	V_{BE}	$V_{CE}=5V, I_C=150mA$			1.5	V
Transition frequency	f_T	$V_{CE}=5V, I_C=150mA$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		12		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank		B	C	D
Range	2SD667	60-120	100-200	160-320
	2SD667A	60-120	100-200	